

AMENDMENTS TO THE CLAIMS

Claims 1-24 were pending prior to entry of the amendments herein. Please cancel Claims 11-15 and 22-24. Please amend Claims 1 and 16. Please add new Claims 25 and 26.

1. (Currently amended) A method of forming a layer of a conductive material on a wafer, wherein a seed layer coats a front surface and an edge surface of the wafer, and wherein the edge surface includes a back edge surface, a bevel surface and a front edge surface, the method comprising the steps of:

removing the seed layer from the back edge surface and the bevel surface; and
forming conductive material onto the seed layer coating the front edge surface and the front surface of the wafer after removing the seed layer from the back edge surface and the bevel surface.

2. (Original) The method of Claim 1, further comprising the step of removing at least a part of the layer which is on the front edge surface.

3. (Original) The method of Claim 1, further comprising rotating the wafer during the step of removing the seed layer.

4. (Original) The method of Claim 3, further comprising the step of applying a process solution onto the back edge surface of the wafer while it is rotated.

5. (Original) The method of Claim 1, wherein the step of removing comprises chemical etching.

6. (Original) The method of Claim 1, wherein the step of removing comprises electrochemical etching.

7. (Original) The method of Claim 2, further comprising rotating the wafer prior to the step of removing the at least a part of the layer.

8. (Original) The method of Claim 7, further comprising the step of applying a process solution to the at least a part of the layer while the wafer is rotated.

9. (Original) The method of Claim 8, wherein the step of removing the at least a part of the layer comprises chemical etching.

10. (Original) The method of Claim 8, wherein the step of removing the at least a part of the layer comprises electrochemical etching.

11. -15. (Canceled)

16. (Currently amended) A method of forming a layer of a conductive material on a wafer comprising a front surface, a back surface and an edge surface, the edge surface including a back edge surface, a bevel surface and a front edge surface, the method comprising the steps of:

depositing a seed layer on the front surface and the edge surface of the wafer;

removing the seed layer from the back edge surface and the bevel surface; and

forming the layer by depositing the conductive material onto the seed layer coating the front edge surface and the front surface after removing the seed layer from the back edge surface and the bevel surface.

17. (Original) The method of Claim 16, further comprising the step of removing a portion of the layer, which is on the front edge surface.

18. (Original) The method of Claim 16, further comprising rotating the wafer during the step of removing the seed layer.

19. (Original) The method of Claim 18, further comprising the step of applying a process solution to the back edge surface while the wafer is rotated.

20. (Original) The method of Claim 16, wherein the step of removing comprises electrochemical removing.

21. (Original) The method of Claim 16, wherein the step of removing comprises chemical removing.

22.-24. (Canceled)

25. (New) The method of Claim 2, wherein the step of removing is after forming the conductive material.

26. (New) The method of Claim 17, wherein the step of removing is after forming the layer.